

# 2N5550 / 2N5551

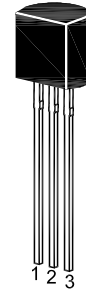
## NPN Silicon Epitaxial Planar Transistors

### Features

- As complementary types the PNP transistors 2N5400 and 2N5401 are recommended.

### Applications

- For general purpose, high voltage amplifier applications



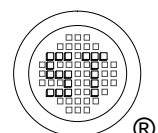
1. Emitter 2. Base 3. Collector  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	2N5550 160	V
2N5551 180			
Collector Emitter Voltage	$V_{CEO}$	2N5550 140	V
2N5551 160			
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_{tot}$	625	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Thermal Characteristics

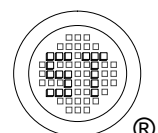
Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$



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### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$ , $I_C = 1\text{ mA}$  at $V_{CE} = 5\text{ V}$ , $I_C = 10\text{ mA}$  at $V_{CE} = 5\text{ V}$ , $I_C = 50\text{ mA}$	2N5550	$h_{FE}$	60	-	-
	2N5551	$h_{FE}$	80	-	-
	2N5550	$h_{FE}$	60	250	-
	2N5551	$h_{FE}$	80	250	-
	2N5550	$h_{FE}$	20	-	-
	2N5551	$h_{FE}$	30	-	-
Collector Base Cutoff Current at $V_{CB} = 100\text{ V}$ at $V_{CB} = 120\text{ V}$	2N5550	$I_{CBO}$	-	100	nA
	2N5551		-	50	
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$		$I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	2N5550	$V_{(BR)CBO}$	160	-	V
	2N5551		180	-	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	2N5550	$V_{(BR)CEO}$	140	-	V
	2N5551		160	-	
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$		$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$ , $I_B = 5\text{ mA}$	2N5550	$V_{CE(sat)}$	-	0.15	V
	2N5551		-	0.25	
	2N5551		-	0.2	
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$ , $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$ , $I_B = 5\text{ mA}$	2N5550	$V_{BE(sat)}$	-	1	V
	2N5551		-	1.2	
	2N5551		-	1	
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$ , $I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$		$f_T$	100	300	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$		$C_{ob}$	-	6	pF



## Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

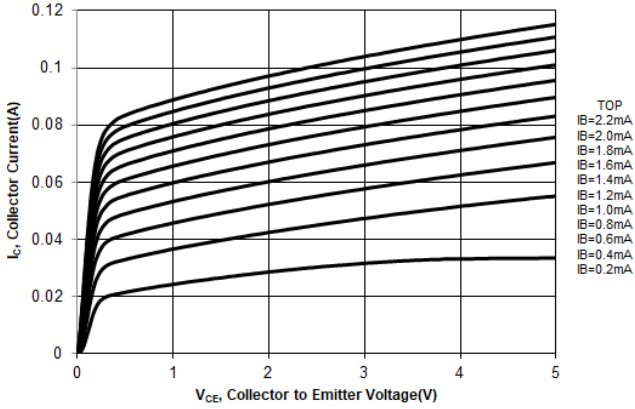


Fig. 2 Collector Current vs. Base to Emitter Voltage

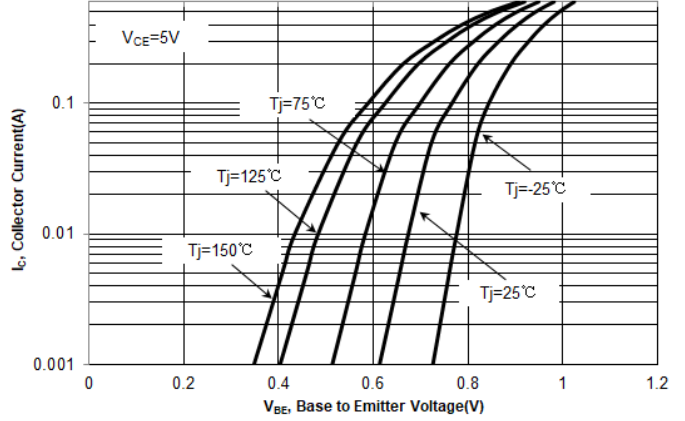


Fig. 3  $h_{FE,DC}$  Current Gain vs. Collector Current

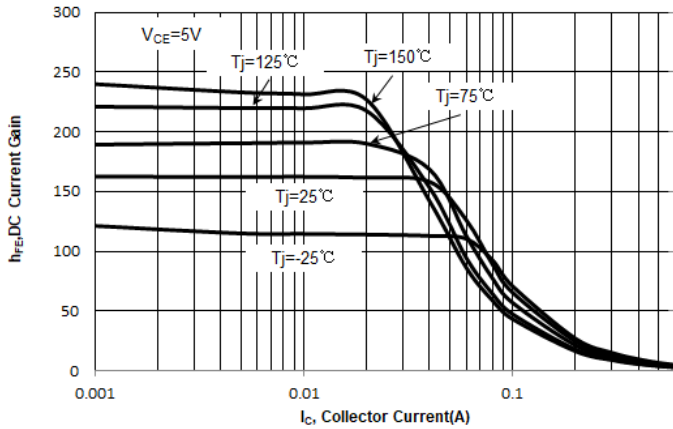
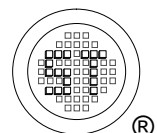
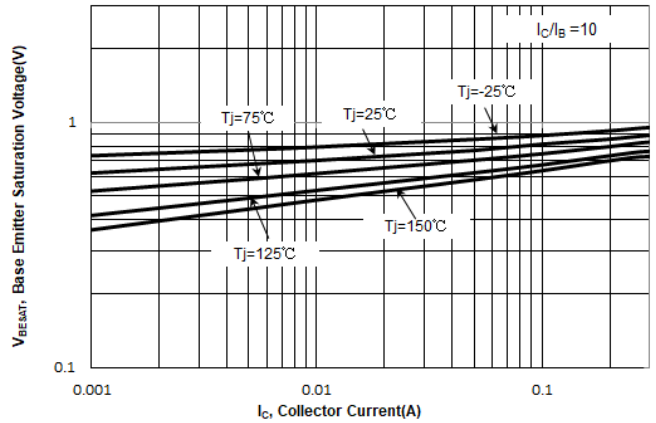


Fig. 4  $V_{BE(sat)}$  vs. Collector Current



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## Electrical Characteristics Curves

Fig. 5  $V_{CE(sat)}$  vs. Collector Current

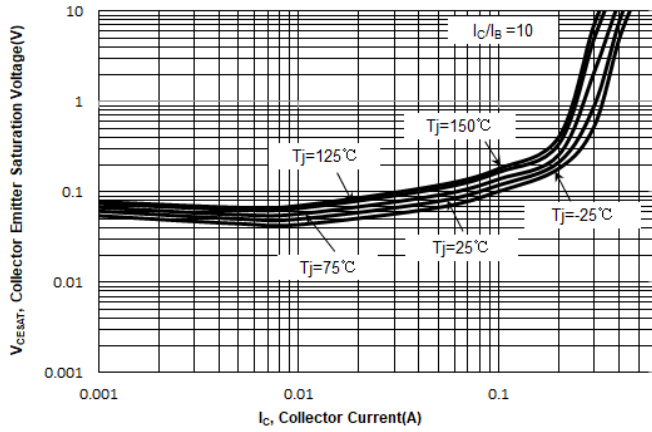


Fig. 6 Junction Capacitance

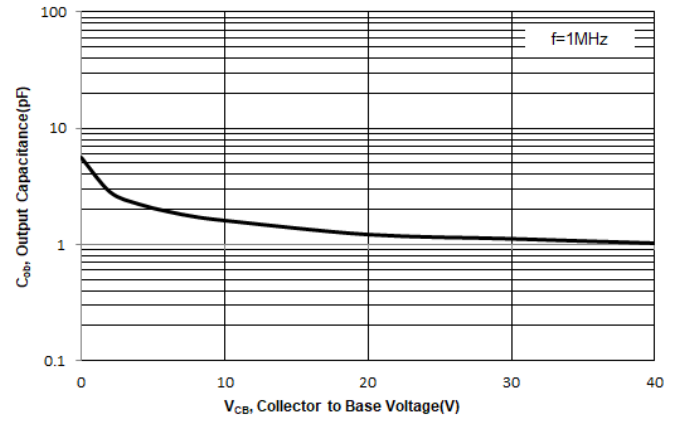
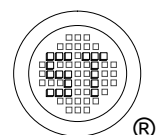
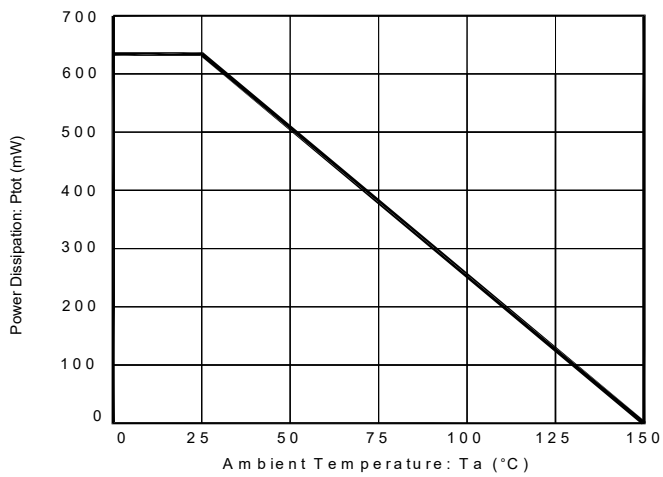
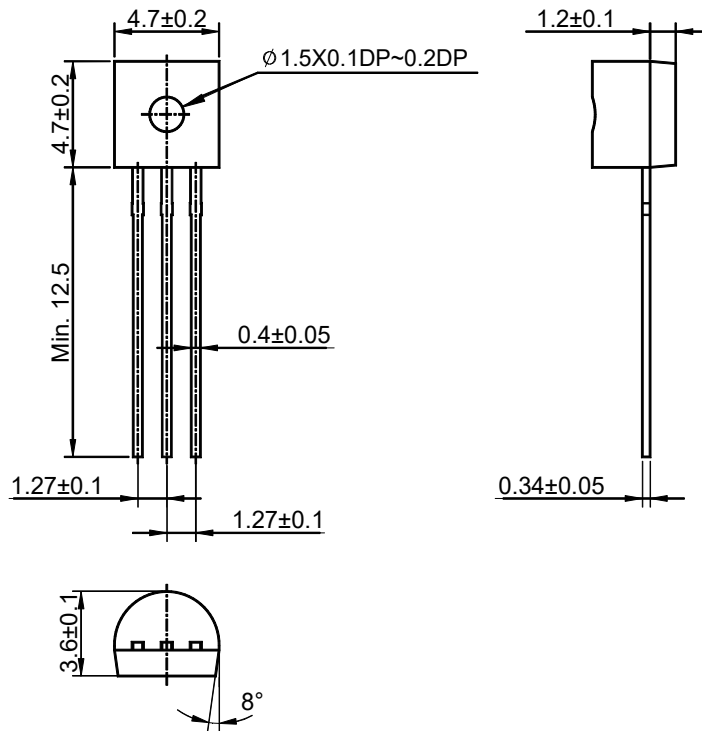


Fig. 7 Power Derating Curve



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## TO-92 Package Outline (Dimensions in millimeters)



## TO-92 Ammo-Pack Outline (Dimensions in millimeters)

